

General Description

The GreenMOS[®] high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS[®] SuperSi series is based on Oriental Semiconductor's unique device design to achieve extremely fast switching characteristics. It is the perfect replacement for the Gallium Nitride (GaN) device in high frequency operations with better ruggedness and cost. It is targeted to meet the most aggressive efficiency standards of power supply systems by pushing both performance and power density to extreme limits.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity




Applications

- PC power
- LED lighting
- Telecom power
- Server power
- EV Charger
- Solar/UPS

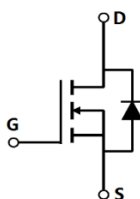
Key Performance Parameters

Parameter	Value	Unit
$V_{DS, min} @ T_{j(max)}$	650	V
$I_{D, pulse}$	90	A
$R_{DS(ON), max} @ V_{GS}=10V$	99	m Ω
Q_g	21.6	nC

Marking Information

Product Name	Package	Marking
OSS60R099KF	TO263	OSS60R099K

Package & Pin Information



Absolute Maximum Ratings at $T_j=25^{\circ}\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	600	V
Gate-source voltage	V_{GS}	± 30	V
Continuous drain current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_D	30	A
Continuous drain current ¹⁾ , $T_C=100^{\circ}\text{C}$		19	
Pulsed drain current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{D, pulse}$	90	A
Continuous diode forward current ¹⁾ , $T_C=25^{\circ}\text{C}$	I_S	30	A
Diode pulsed current ²⁾ , $T_C=25^{\circ}\text{C}$	$I_{S, pulse}$	90	A
Power dissipation ³⁾ , $T_C=25^{\circ}\text{C}$	P_D	219	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	577.6	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\dots 480\text{ V}$, $I_{SD}\leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^{\circ}\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	0.57	$^{\circ}\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62.5	$^{\circ}\text{C/W}$

Electrical Characteristics at $T_j=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	600			V	$V_{GS}=0\text{ V}$, $I_D=250\ \mu\text{A}$
		650	740			$V_{GS}=0\text{ V}$, $I_D=250\ \mu\text{A}$, $T_j=150^{\circ}\text{C}$
Gate threshold voltage	$V_{GS(th)}$	2.9		3.9	V	$V_{DS}=V_{GS}$, $I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$		0.080	0.099	Ω	$V_{GS}=10\text{ V}$, $I_D=15\text{ A}$
			0.192			$V_{GS}=10\text{ V}$, $I_D=15\text{ A}$, $T_j=150^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=600\text{ V}$, $V_{GS}=0\text{ V}$

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		1282.1		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$
Output capacitance	C_{oss}		235.9		pF	
Reverse transfer capacitance	C_{rss}		9.1		pF	
Turn-on delay time	$t_{d(on)}$		24.9		ns	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $R_G=2\ \Omega$, $I_D=20\text{ A}$
Rise time	t_r		32.3		ns	
Turn-off delay time	$t_{d(off)}$		42.3		ns	
Fall time	t_f		27.5		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		21.6		nC	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $I_D=20\text{ A}$
Gate-source charge	Q_{gs}		6.9		nC	
Gate-drain charge	Q_{gd}		7.8		nC	
Gate plateau voltage	$V_{plateau}$		6.5		V	

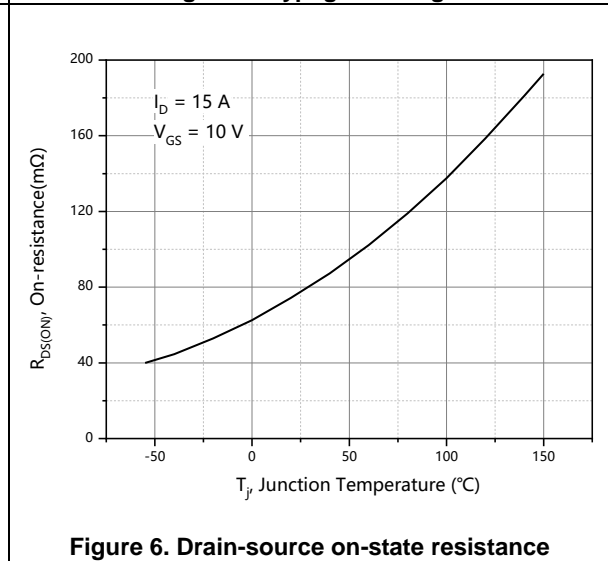
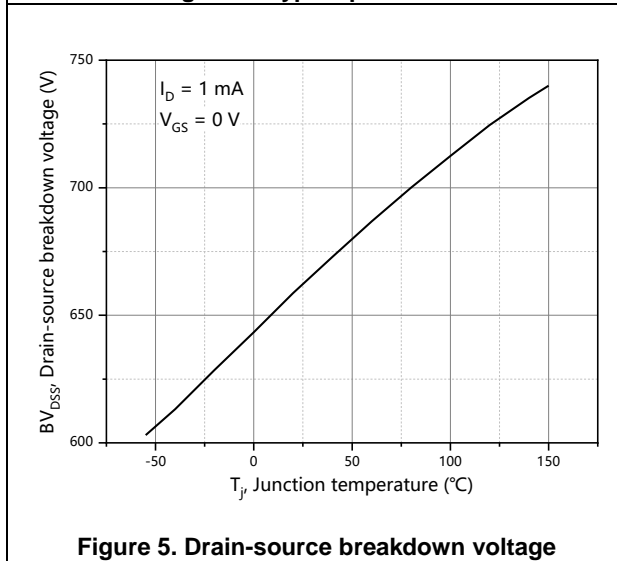
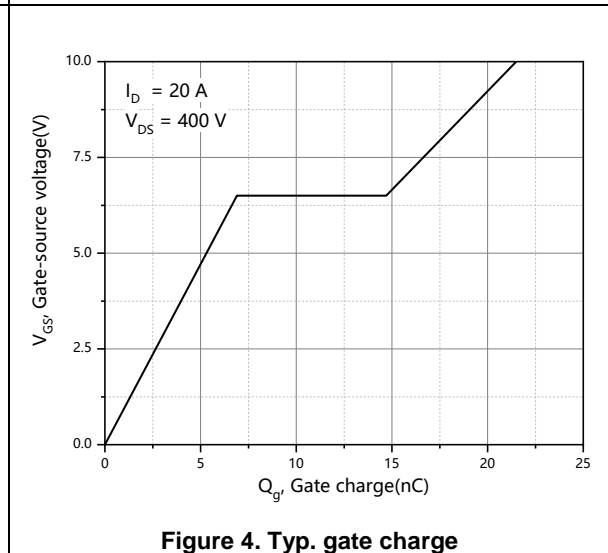
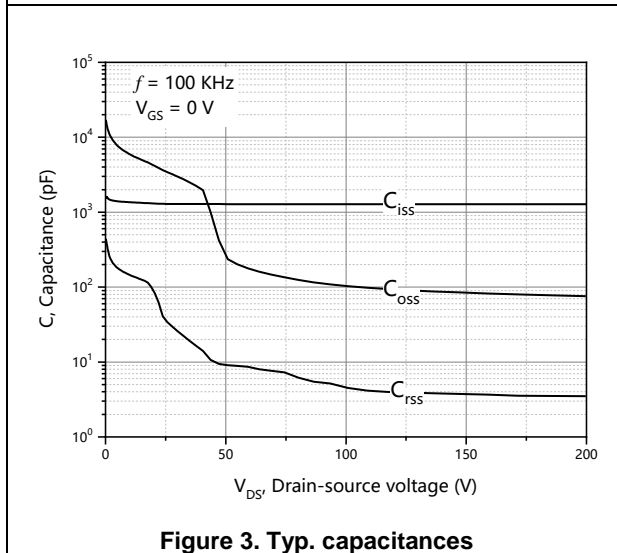
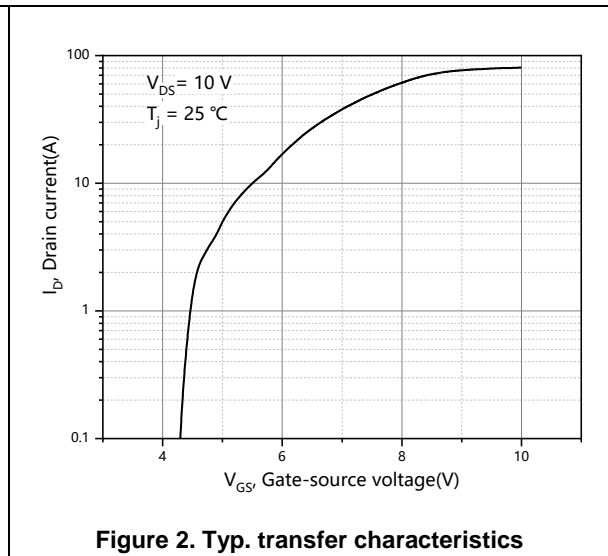
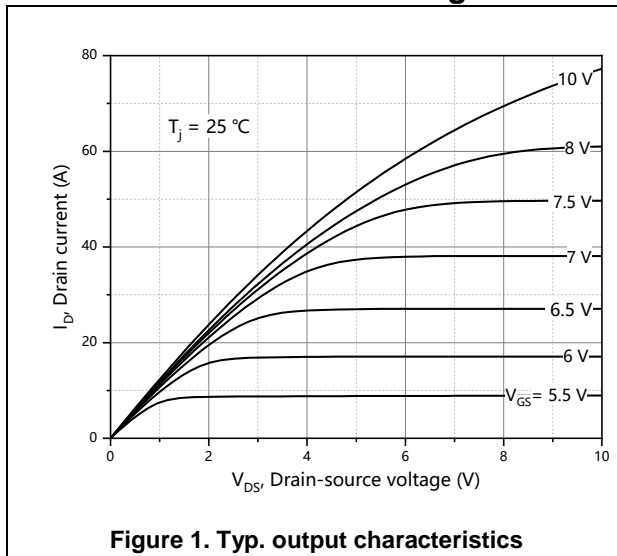
Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.4	V	$I_S=30\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		416.0		ns	$V_R=400\text{ V}$, $I_S=20\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		6.8		μC	
Peak reverse recovery current	I_{rrm}		32.1		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.
- 5) $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $L=60\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams



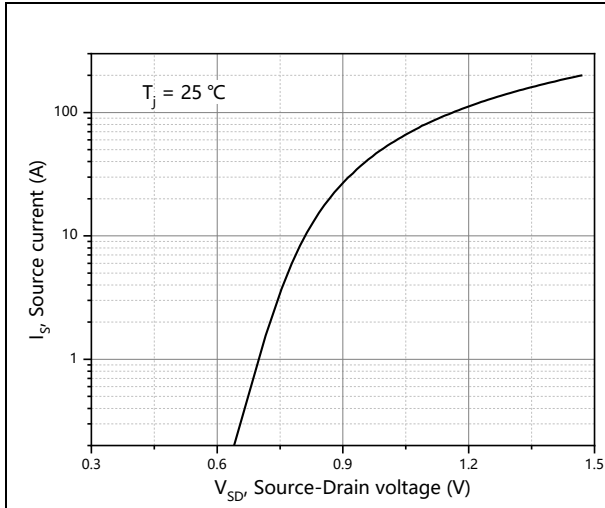


Figure 7. Forward characteristic of body diode

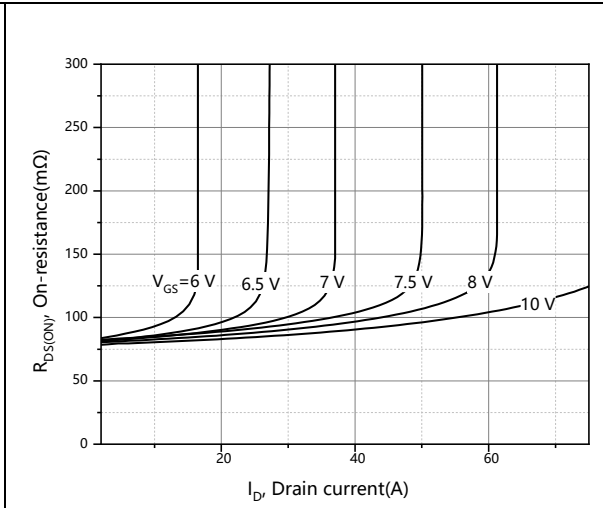


Figure 8. Drain-source on-state resistance

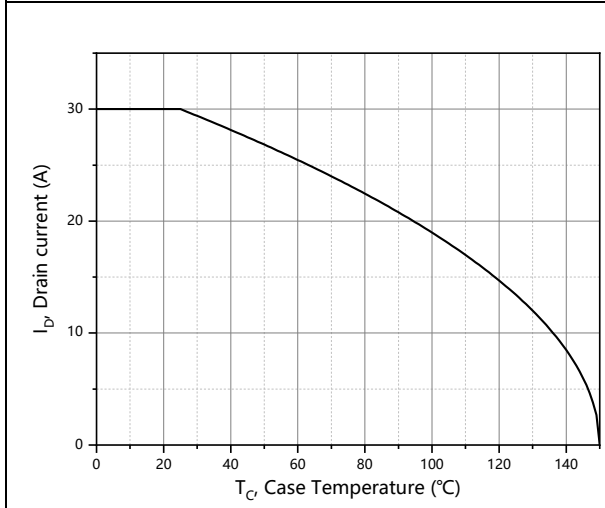


Figure 9. Drain current

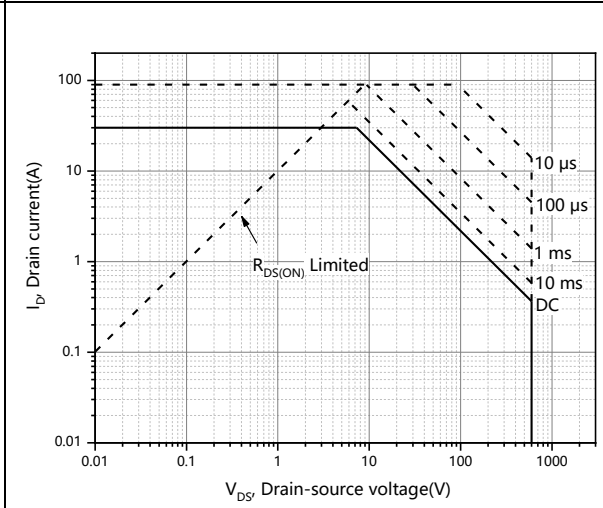


Figure 10. Safe operation area T_C=25 °C

Test circuits and waveforms



Figure 1. Gate charge test circuit & waveform



Figure 2. Switching time test circuit & waveforms

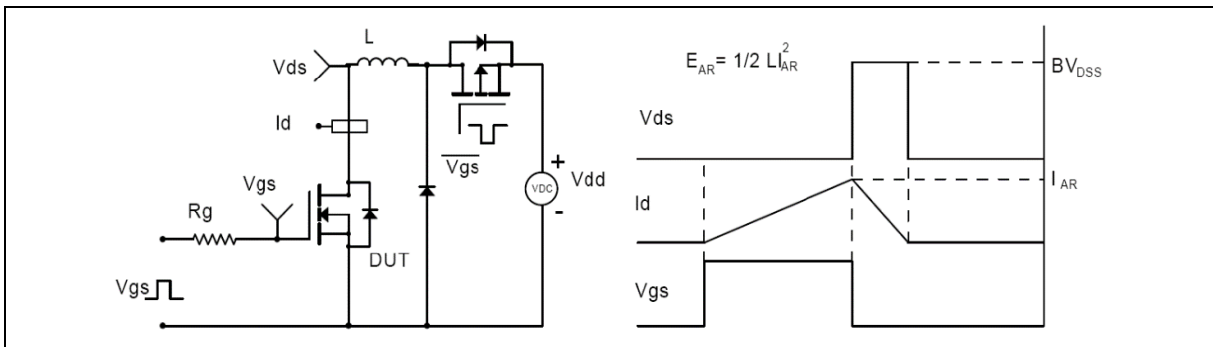
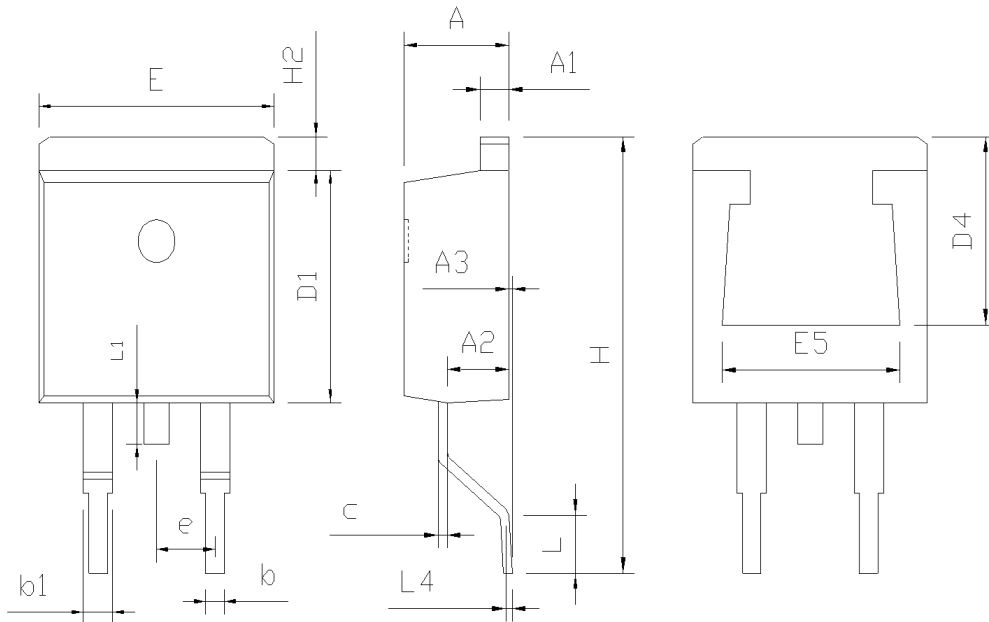


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms



Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm		
	Min	Nom	Max
A	4.37	4.57	4.77
A1	1.22	1.27	1.42
A2	2.49	2.69	2.89
A3	0.00	0.13	0.25
b	0.70	0.81	0.96
b1	1.17	1.27	1.47
c	0.30	0.38	0.53
D1	8.50	8.70	8.90
D4	6.60	-	-
E	9.86	10.16	10.36
E5	7.06	-	-
e	2.54BSC		
H	14.70	15.10	15.50
H2	1.07	1.27	1.47
L	2.00	2.30	2.60
L1	1.40	1.55	1.70
L4	0.25BSC		

Version 1: TO263-C package outline dimension

Ordering Information

Package Type	Units/ Reel	Reels/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
TO263-C	800	1	800	5	4000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSS60R099KF	TO263	yes	yes	yes

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